

X3-Class HiPerFET™ Power MOSFET

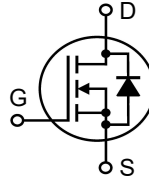
IXFT120N30X3HV IXFH120N30X3

$$V_{DSS} = 300V$$

$$I_{D25} = 120A$$

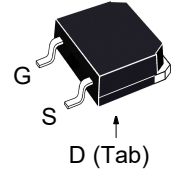
$$R_{DS(on)} \leq 11.0m\Omega$$

N-Channel Enhancement Mode
Avalanche Rated

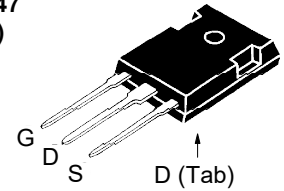


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	300	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	300	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	120	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	280	A
I_A	$T_C = 25^\circ C$	60	A
E_{AS}	$T_C = 25^\circ C$	2	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	50	V/ns
P_D	$T_C = 25^\circ C$	735	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247	6	g

TO-268HV
(IXFT..HV)



TO-247
(IXFH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4mA$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1	8.6	11.0	m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	60	100	S
R_{Gi}	Gate Input Resistance		1.7	Ω
C_{iss}	} $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		10.5	nF
C_{oss}			1376	pF
C_{rss}			3	pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related } $V_{GS} = 0\text{V}$		530	pF
$C_{o(tr)}$	Time related } $V_{DS} = 0.8 \cdot V_{DSS}$		2100	pF
$t_{d(on)}$	} Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		30	ns
t_r			30	ns
$t_{d(off)}$			130	ns
t_f			14	ns
$Q_{g(on)}$	} $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		170	nC
Q_{gs}			50	nC
Q_{gd}			50	nC
R_{thJC}	TO-247			0.17 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			120 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			480 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	} $I_F = 60\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		145	ns
Q_{RM}			930	nC
I_{RM}			13	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Littelfuse Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
by one or more of the following U.S. patents:	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

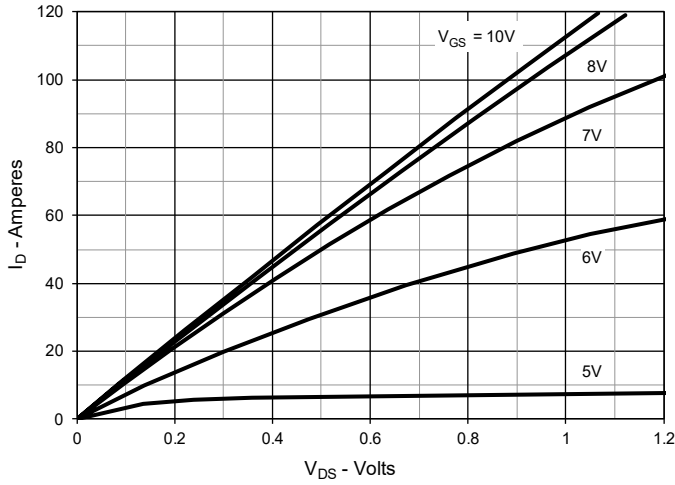


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

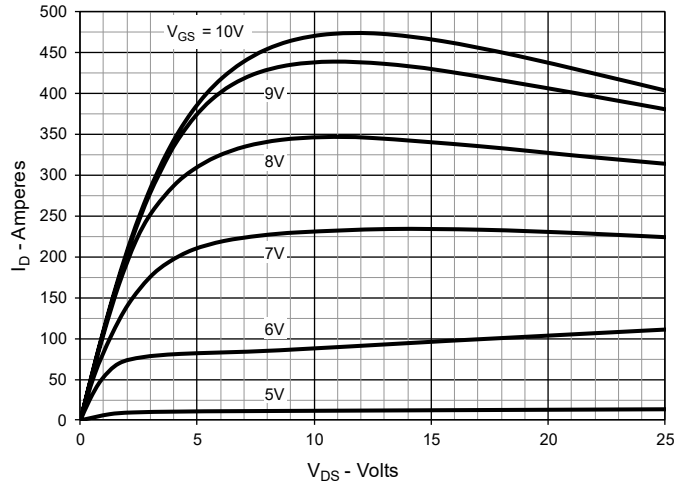


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

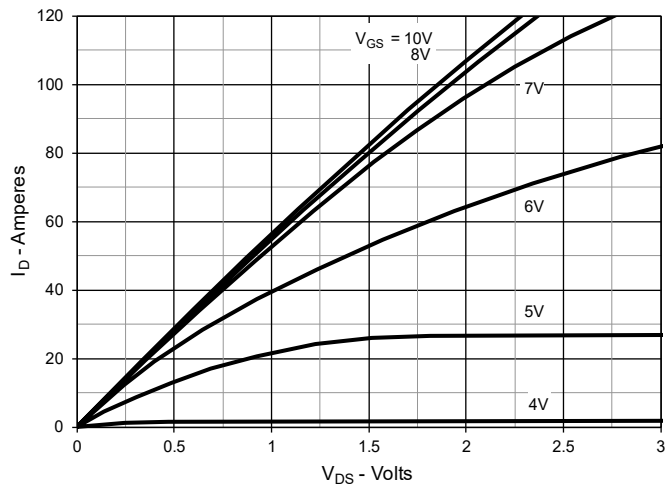


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 60\text{A}$ Value vs. Junction Temperature

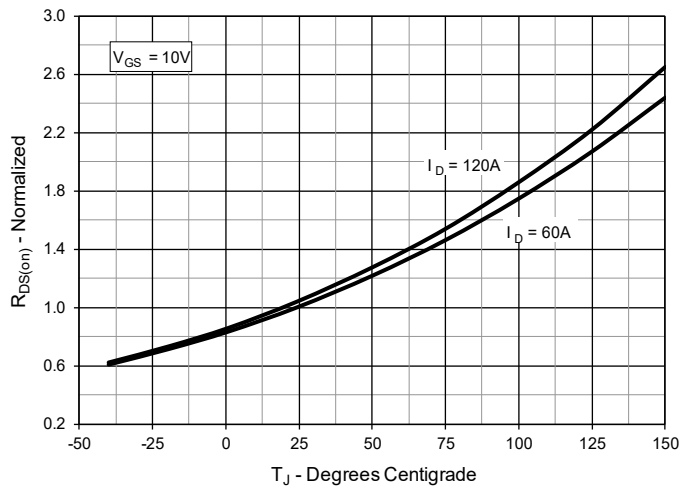


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 60\text{A}$ Value vs. Drain Current

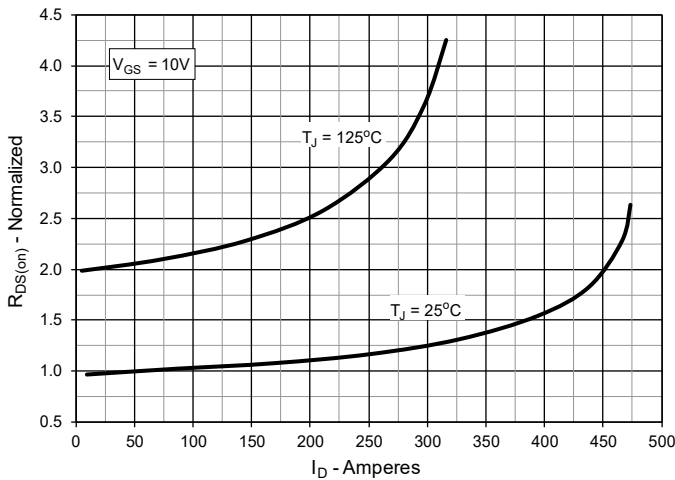


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

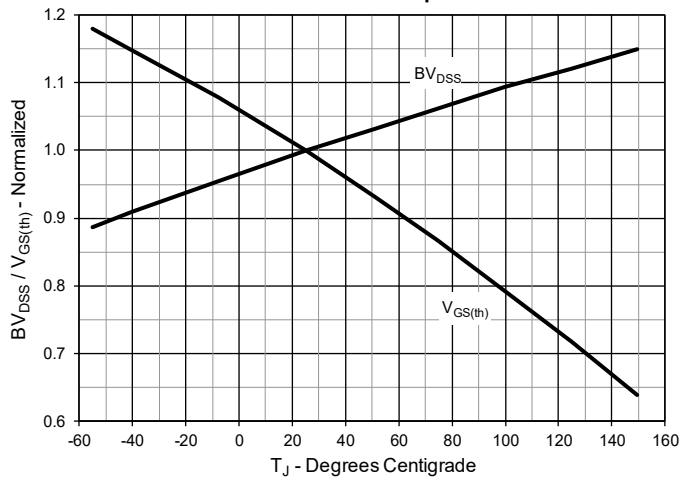


Fig. 7. Maximum Drain Current vs. Case Temperature

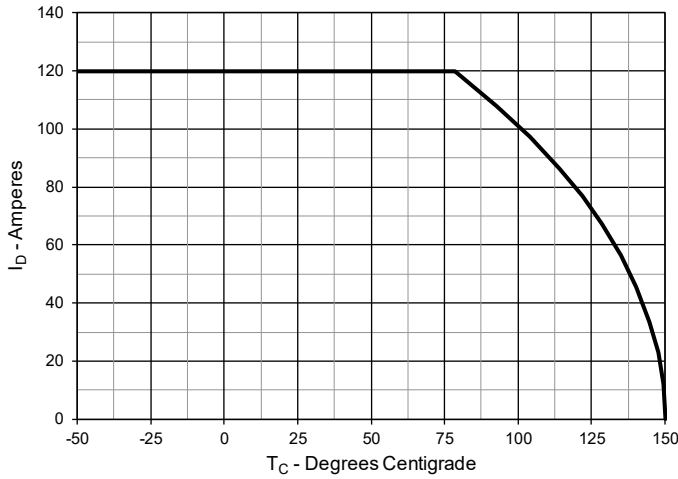


Fig. 8. Input Admittance

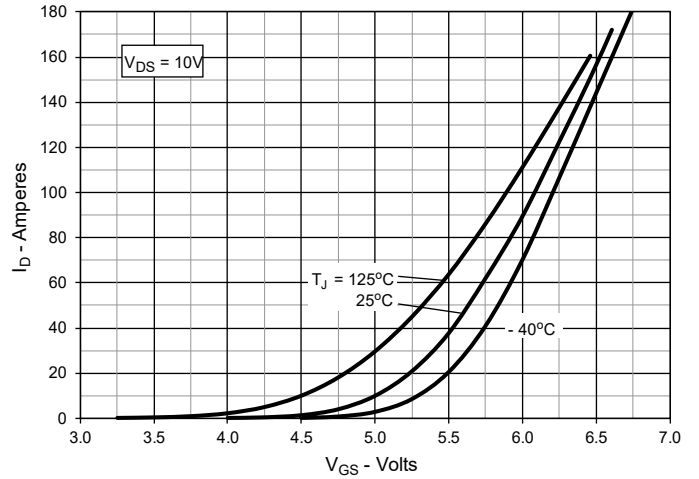


Fig. 9. Transconductance

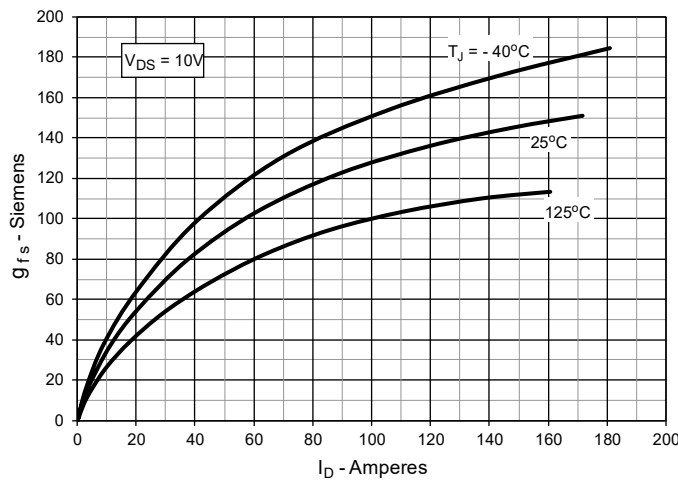


Fig. 10. Forward Voltage Drop of Intrinsic Diode

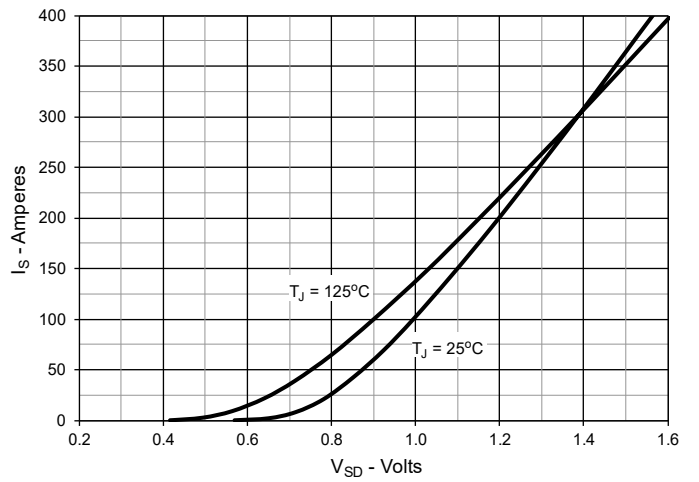


Fig. 11. Gate Charge

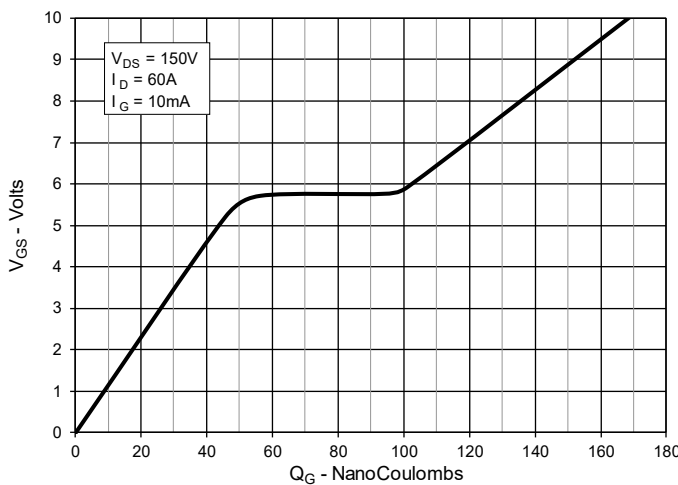


Fig. 12. Capacitance

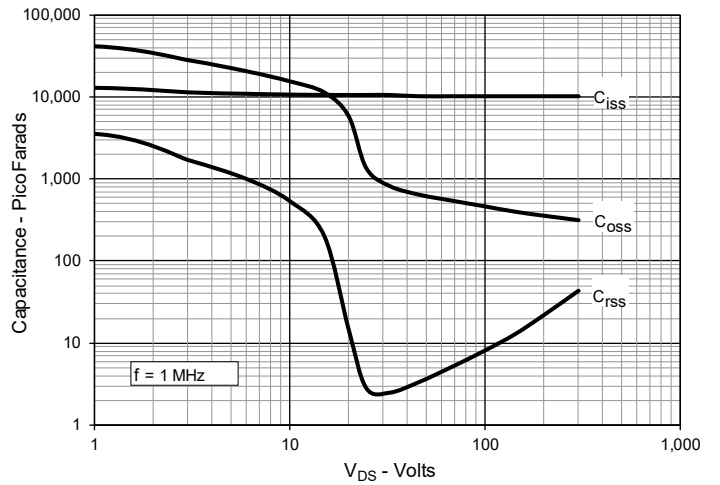


Fig. 13. Output Capacitance Stored Energy

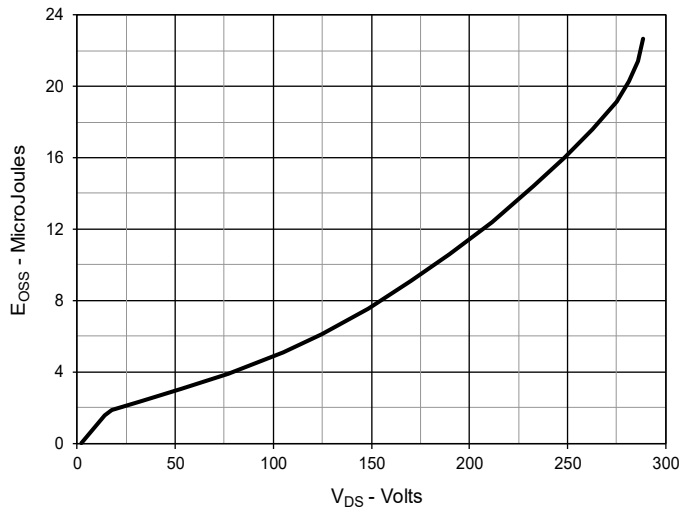


Fig. 14. Forward-Bias Safe Operating Area

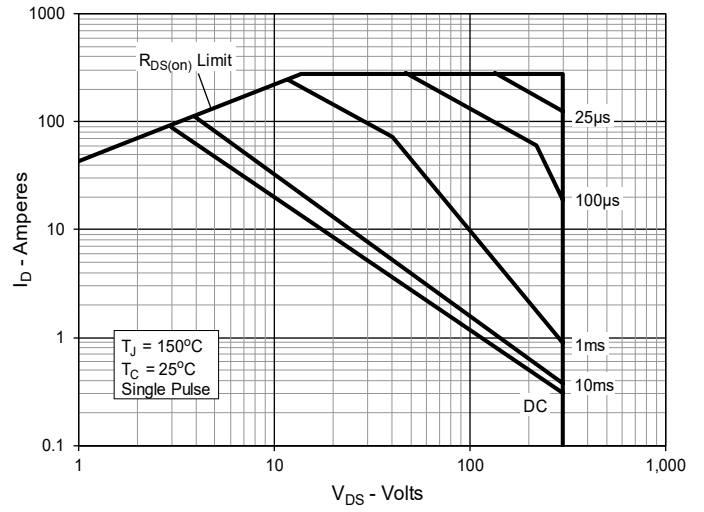
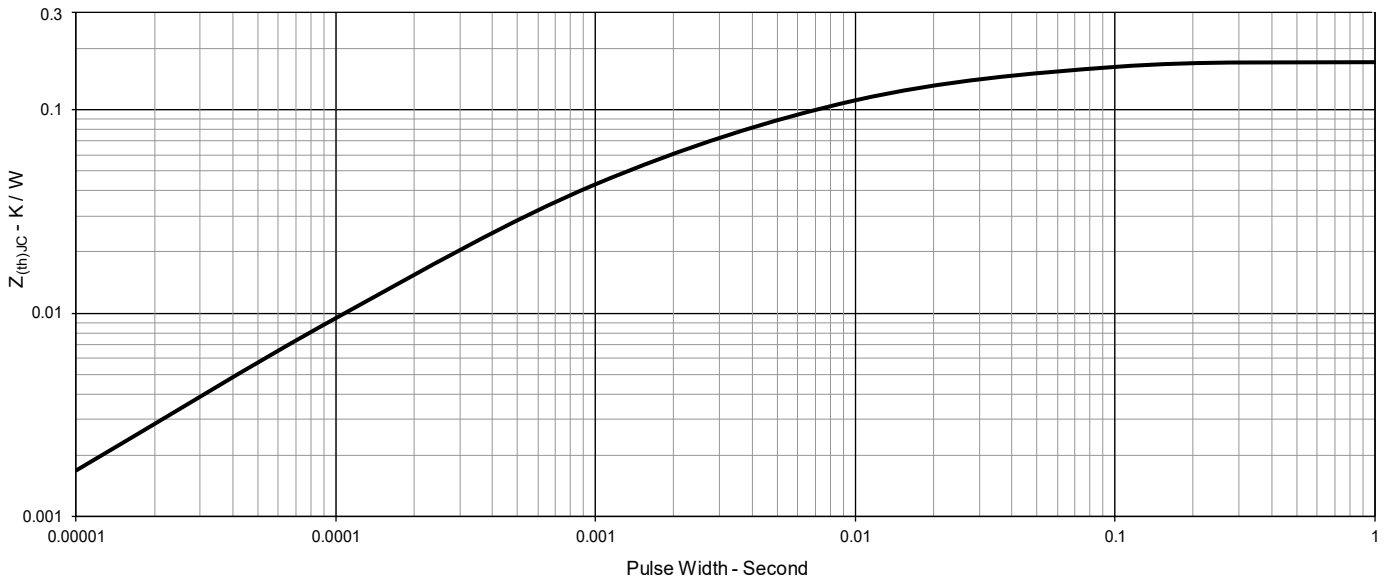
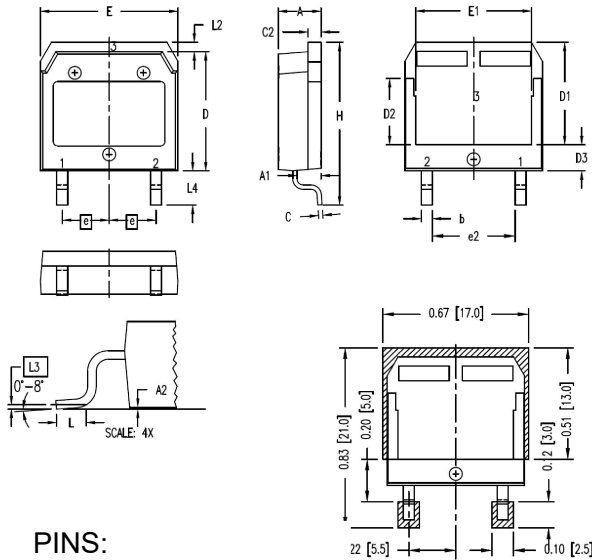


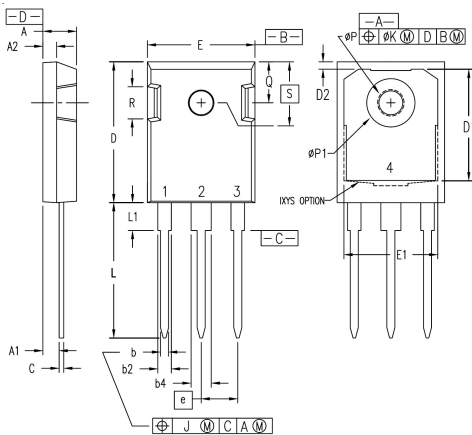
Fig. 15. Maximum Transient Thermal Impedance



TO-268HV Outline

PINS:

- 1 - Gate
- 2 - Source
- 3 - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

TO-247 Outline

PINS:

- 1 - Gate
- 2 - Drain
- 3 - Source

SYM	INCHES		INCHES	
	MIN	MAX	MIN	MAX
A	0.190	0.205	4.83	5.21
A1	0.090	0.100	2.29	2.54
A2	0.075	0.085	1.91	2.16
b	0.045	0.055	1.14	1.40
b2	0.075	0.087	1.91	2.20
b4	0.115	0.126	2.92	3.20
C	0.024	0.031	0.61	0.80
D	0.819	0.840	20.80	21.34
D1	0.650	0.690	16.51	17.53
D2	0.035	0.050	0.89	1.27
E	0.620	0.635	15.57	16.13
E1	0.545	0.565	13.84	14.35
e	0.215 BSC		5.45 BSC	
J	--	0.010	--	0.250
K	--	0.025	--	0.640
L	0.780	0.810	19.81	20.57
L1	0.150	0.170	3.81	4.32
ØP	0.140	0.144	3.55	3.65
ØP1	0.275	0.290	6.99	7.37
Q	0.220	0.244	5.59	6.20
R	0.170	0.190	4.32	4.83
S	0.242 BSC		6.15 BSC	

